



9014

NPN SILICON TRANSISTOR

FEATURES

Power dissipation

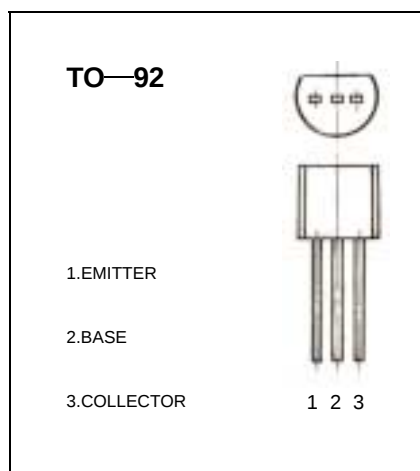
$P_{CM} : 0.4 \text{ W}$ ($T_{amb}=25^{\circ}\text{C}$)

Collector current

$I_{CM} : 0.1 \text{ A}$

Collector-base voltage

$V_{(BR)CBO} : 50 \text{ V}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu\text{A}$, $I_E = 0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1 \text{ mA}$, $I_B = 0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu\text{A}$, $I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 50 \text{ V}$, $I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 35 \text{ V}$, $I_B = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3 \text{ V}$, $I_C = 0$			0.1	μA
DC current gain(note)	$H_{FE(1)}$	$V_{CE} = 5 \text{ V}$, $I_C = 1 \text{ mA}$	60		1000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}$, $I_B = 5 \text{ mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 100 \text{ mA}$, $I_B = 5 \text{ mA}$			1	V
Transition frequency	f_T	$V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$ $f = 30 \text{ MHz}$	150			MHz

CLASSIFICATION OF $H_{FE(1)}$

Rank	A	B	C	D
Range	60-150	100-300	200-600	400-1000